

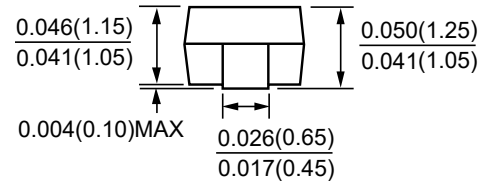
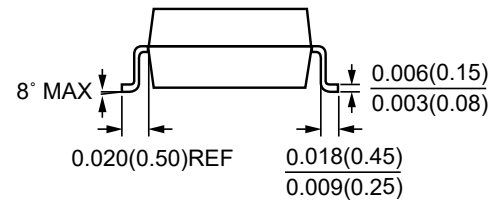
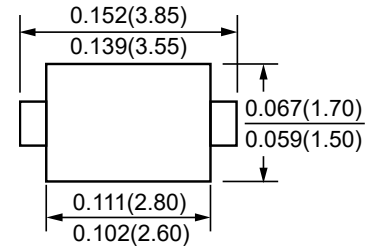


FEATURES

- ◆ Low Forward Voltage Drop
- ◆ Guard Ring Construction for Transient Protection
- ◆ Negligible Reverse Recovery Time
- ◆ Low Reverse Capacitance
- ◆ Marking :
SD103AW : S4
SD103BW : S5
SD103CW : S6

SOD-123

Unit:inch(mm)



MAXIMUM RATINGS, SINGLE DIODE @TA=25°C

Parameter	Symbol	SD103AW	SD103BW	SD103CW	Unit
Peak Repetitive Peak reverse voltage	V_{RRM}				
Working Peak	V_{RWM}	40	30	20	V
DC Blocking Voltage	V_R				
RMS Reverse Voltage	$V_{R(RMS)}$	28	21	14	V
Average Forward Rectified Current	I_{FM}		350		mA
Non-Repetitive Peak Forward Surge @ $t \leq 8.3ms$	I_{FSM}		2		A
Power Dissipation	P_D		400		mW
Junction Temperature	T_J		125		°C
Storage Temperature Range	T_{STG}		-55~+150		°C

DEVICE CHARACTERISTICS

SD103AW/ BW/ CW

ELECTRICAL CHARACTERISTICS @ TA=25°C

Parameter	Test conditions	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	$I_F=20\text{mA}$	V_F	—	—	0.37	V
	$I_F=200\text{mA}$		—	—	0.6	
Reverse Current	SD103AW $V_R=30\text{V}$	I_{RM}	—	—	5	μA
	SD103BW $V_R=20\text{V}$					
	SD103CW $V_R=10\text{V}$					
Capacitance Between Terminals	$V_R=0, f=1\text{MHz}$	C_T	—	50	—	pF
Reverse Recovery Time	$I_F=I_R=200\text{mA}$, $I_{rr}=0.1I_R$, $R_L=100\Omega$	t_{rr}	—	10	—	ns

CHARACTERISTICS CURVES

FIG. 1-Forward Characteristics

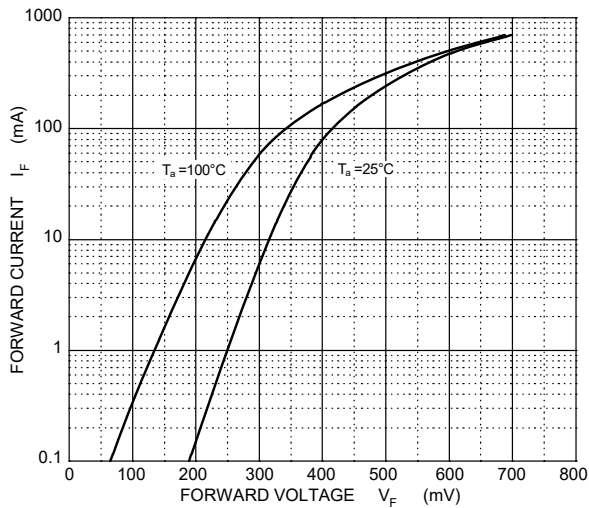


FIG. 2-Capacitance

